
Residual Gas Composition during Diamond Deposition with a New Developed Microwave Surface Wave Plasma Source

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Microwave plasma chemical vapor deposition (MPCVD) has made great progress, and is considered as one of the most promising techniques for mass production of large size and high quality single and/or poly crystalline diamond [1-4]. Homoepitaxial growth of single crystalline diamond by MPCVD has been reported to obtain inch-size diamond with fast growth rate and improved diamond quality [5]. Nanodiamond has many distinctive inherent properties such as high hardness, superior thermal conductivity, high refraction index, and extraordinary resistivity, allowing it to be a promising material for various kinds of applications [6]. However, the growth parameters, like deposition temperature, pressure, feeding gas composition and microwave power, have a strong influence on the morphology and crystal quality of the growth surface [3].

The objectives of this work is to investigate the influence of residual gas composition on deposited diamond film parameters [7] during MPCVD with a compact surface wave plasma(SWP) source [8-9]. The newly developed SWP source is employed for diamond film deposition with H₂/CH₄ operation. Stable plasma is maintained in conditions of different flow rates and 2-2.5 kW microwave power range. Decompositions of CH₄/H₂ are measured with residual gas analyzer (RGA). Microwave plasma parameters are also measured with fast-scanning Langmuir probe. Wafer temperature is controlled with sample heater. Deposited films characterizations are investigated at different CH₄/H₂ ratios, operating pressures, flowrates and wafer temperatures. Optimum mode of SWP source operation for diamond films deposition is discussed.

[1] J. Chen et al. *Journal of Crystal Growth* 484 (2018) 1–6 <https://doi.org/10.1016/j.jcrysgro.2017.12.022>

[2] R.J. Nemanich et al. *MRS Bull.* 39 (2014) 490–494. <https://doi.org/10.1557/mrs.2014.97>

[3] C.J. Widmann et al. *Diamond Relat. Mater.* 64 (2016) 1–7. <https://doi.org/10.1016/j.diamond.2015.12.016>

[4] Q. Liang et al. *Diamond Relat. Mater.* 18 (5–8) (2009) 698–703. <https://doi.org/10.1016/j.diamond.2008.12.002>

[5] H. Yamada et al. *Appl. Phys. Lett.* 104 (10) (2014) 102110. <https://doi.org/10.1063/1.4868720>

[6] Y. Zhang et al. *Composites Part B* 143 (2018) 19–27. <https://doi.org/10.1016/j.compositesb.2018.01.028>

[7] M.K. Han et al. *J Electr Eng Technol.* 2017; 12(5): 2007-2013. <http://doi.org/10.5370/JEET.2017.12.5.2007>

[8] H.J. You and W.I. Choo. Development of a water-cooled compact surface wave plasma source for remote plasma processing. 33th International Conference on Phenomena in Ionized Gases, Portugal 2017, PIV.69

[9] W.I. Choo and H.J. You. Study on high flow rate F-radical generation by a compact water-cooled surface wave plasma source for remote plasma cleaning process. 33th International Conference on Phenomena in Ionized Gases, Portugal 2017, PII.22

This work was supported by R&D Program of ‘Plasma Convergence & Fundamental Research’ through the National Fusion Research Institute of Korea (NFRI) funded by the Government funds.